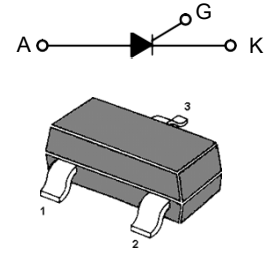


# MCR100 Series

## Sensitive Gate Silicon Controlled Rectifiers

### Features

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 V
- On-State Current Rating of 0.8 Amperes RMS at 80°C
- High Surge Current Capability – 10 A
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to  $dV/dt$  – 20 V/ $\mu$ sec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity



1. SOT-23 Plastic Package

2. MARKING:

MCR100-3:100-3  
MCR100-4:100-4  
MCR100-5:100-5  
MCR100-6:100-6  
MCR100-7:100-7  
MCR100-8:100-8

| PIN ASSIGNMENT |         |
|----------------|---------|
| 1              | Cathode |
| 2              | Gate    |
| 3              | Anode   |

### MAXIMUM RATINGS ( $T_J=25^\circ\text{C}$ unless otherwise noted.)

| Rating                                                                                                                         | Symbol                                      | Value                                  | Unit                 |
|--------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------|----------------------------------------|----------------------|
| Peak Repetitive Forward and Reverse Blocking Voltage, Note 1<br>( $T_J=25$ to $125^\circ\text{C}$ , $R_{GK}=1\text{K}\Omega$ ) | $V_{\text{DRM}}$<br>and<br>$V_{\text{RRM}}$ | 100<br>200<br>300<br>400<br>500<br>600 | Volts                |
| Forward Current RMS<br>(All Conduction Angles)                                                                                 | $I_{\text{T(RMS)}}$                         | 0.8                                    | Amps                 |
| Peak Forward Surge Current, $T_A=25^\circ\text{C}$<br>(1/2 Cycle, Sine Wave, 60Hz)                                             | $I_{\text{TSM}}$                            | 10                                     | Amps                 |
| Circuit Fusing ( $t=8.3\text{ms}$ )                                                                                            | $I^2t$                                      | 0.415                                  | $\text{A}^2\text{s}$ |
| Peak Gate Power - Forward, $T_A=25^\circ\text{C}$                                                                              | $P_{\text{GM}}$                             | 0.1                                    | Watts                |
| Average Gate Power - Forward, $T_A=25^\circ\text{C}$                                                                           | $P_{\text{GF(AV)}}$                         | 0.01                                   | Watt                 |
| Peak Gate Current - Forward, $T_A=25^\circ\text{C}$<br>(300 $\mu$ s, 120PPS)                                                   | $I_{\text{GFM}}$                            | 1                                      | Amp                  |
| Peak Gate Voltage - Reverse                                                                                                    | $V_{\text{GRM}}$                            | 5                                      | Volts                |
| Operating Junction Temperature Range @ Rated $V_{\text{RRM}}$ and $V_{\text{DRM}}$                                             | $T_J$                                       | -40 to +125                            | $^\circ\text{C}$     |
| Storage Temperature Range                                                                                                      | $T_s$                                       | -40 to +150                            | $^\circ\text{C}$     |

Note 1. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode.

## THERMAL CHARACTERISTICS

| Characteristic                                                 | Symbol                             | Max       | Unit                 |
|----------------------------------------------------------------|------------------------------------|-----------|----------------------|
| Thermal Resistance, Junction-to-Case<br>Junction-to-Ambient    | $R_{\theta JC}$<br>$R_{\theta JA}$ | 75<br>200 | $^{\circ}\text{C/W}$ |
| Lead Solder Temperature<br>( $<1/16''$ from case, 10 secs max) | $T_L$                              | 260       | $^{\circ}\text{C}$   |

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                                                                                    |                    |   |   |           |               |
|----------------------------------------------------------------------------------------------------------------------------------------------------|--------------------|---|---|-----------|---------------|
| Peak Repetitive Forward or Reverse Blocking Current (Note 2)<br>( $V_D = \text{Rated } V_{DRM} \text{ and } V_{RRM}; R_{GK} = 1 \text{ k}\Omega$ ) | $I_{DRM}, I_{RRM}$ | - | - | 10<br>100 | $\mu\text{A}$ |
| $T_C = 25^{\circ}\text{C}$<br>$T_C = 110^{\circ}\text{C}$                                                                                          |                    | - | - |           |               |

### ON CHARACTERISTICS

|                                                                                                   |          |   |           |            |               |
|---------------------------------------------------------------------------------------------------|----------|---|-----------|------------|---------------|
| Peak Forward On-State Voltage*<br>( $I_{TM} = 1.0 \text{ A Peak @ } T_A = 25^{\circ}\text{C}$ )   | $V_{TM}$ | - | -         | 1.7        | V             |
| Gate Trigger Current (Continuous dc) (Note 3)<br>( $V_{AK} = 7.0 \text{ Vdc}, R_L = 100 \Omega$ ) | $I_{GT}$ | - | 40        | 200        | $\mu\text{A}$ |
| Holding Current <sup>(2)</sup><br>( $V_{AK} = 7.0 \text{ Vdc}$ , Initiating Current = 20 mA)      | $I_H$    | - | 0.5<br>-  | 5.0<br>10  | mA            |
| Latch Current<br>( $V_{AK} = 7.0 \text{ V}$ , $I_g = 200 \mu\text{A}$ )                           | $I_L$    | - | 0.6<br>-  | 10<br>15   | mA            |
| Gate Trigger Voltage (Continuous dc) (Note 3)<br>( $V_{AK} = 7.0 \text{ Vdc}, R_L = 100 \Omega$ ) | $V_{GT}$ | - | 0.62<br>- | 0.8<br>1.2 | V             |
| $T_C = 25^{\circ}\text{C}$<br>$T_C = -40^{\circ}\text{C}$                                         |          | - | -         |            |               |

### DYNAMIC CHARACTERISTICS

|                                                                                                                                                                      |         |    |    |    |                        |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|----|----|----|------------------------|
| Critical Rate of Rise of Off-State Voltage<br>( $V_D = \text{Rated } V_{DRM}$ , Exponential Waveform, $R_{GK} = 1000 \Omega, T_J = 110^{\circ}\text{C}$ )            | $dV/dt$ | 20 | 35 | -  | $\text{V}/\mu\text{s}$ |
| Critical Rate of Rise of On-State Current<br>( $I_{PK} = 20 \text{ A}$ ; $P_w = 10 \mu\text{sec}$ ; $di/dt = 1 \text{ A}/\mu\text{sec}$ , $I_{gt} = 20 \text{ mA}$ ) | $di/dt$ | -  | -  | 50 | $\text{A}/\mu\text{s}$ |

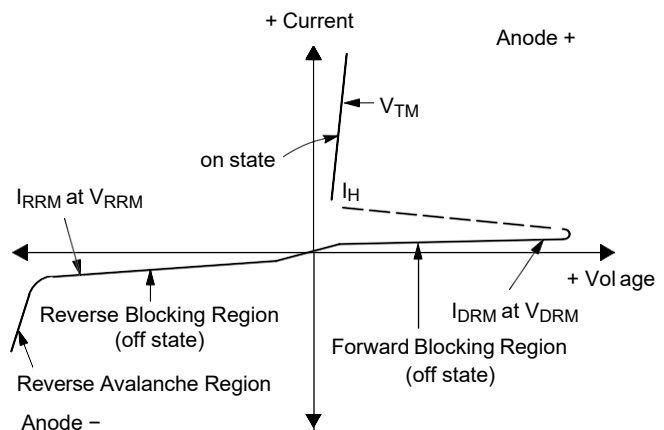
\*Indicates Pulse Test: Pulse Width  $\leq 1.0 \text{ ms}$ , Duty Cycle  $\leq 1\%$ .

2.  $R_{GK} = 1000 \Omega$  included in measurement.

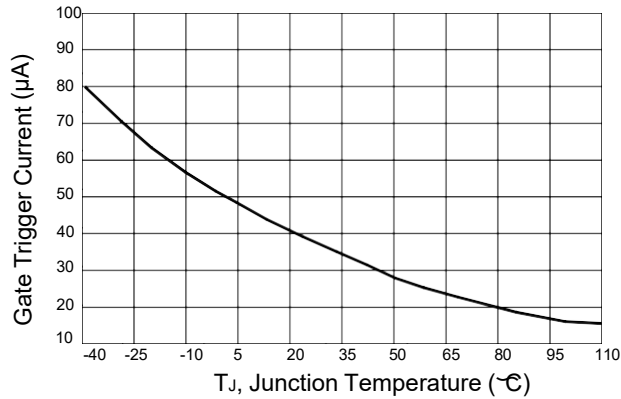
3. Does not include  $R_{GK}$  in measurement.

## Voltage Current Characteristic of SCR

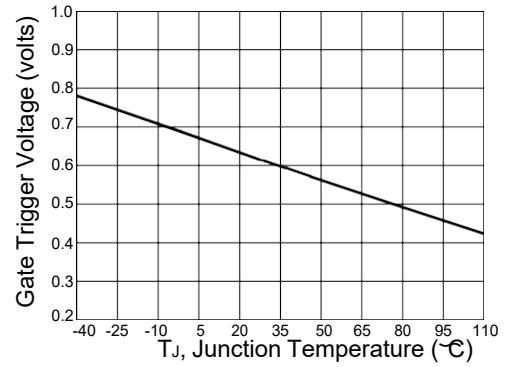
| Symbol    | Parameter                                 |
|-----------|-------------------------------------------|
| $V_{DRM}$ | Peak Repetitive Off State Forward Voltage |
| $I_{DRM}$ | Peak Forward Blocking Current             |
| $V_{RRM}$ | Peak Repetitive Off State Reverse Voltage |
| $I_{RRM}$ | Peak Reverse Blocking Current             |
| $V_{TM}$  | Peak on State Voltage                     |
| $I_H$     | Holding Current                           |



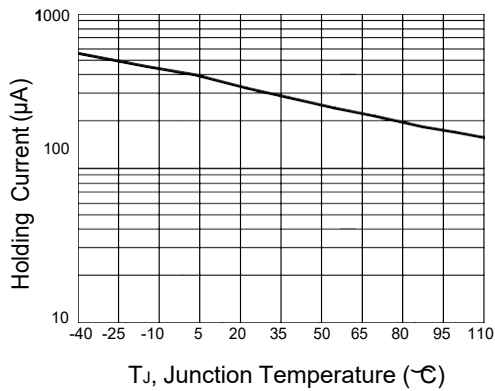
## Typical Characteristics



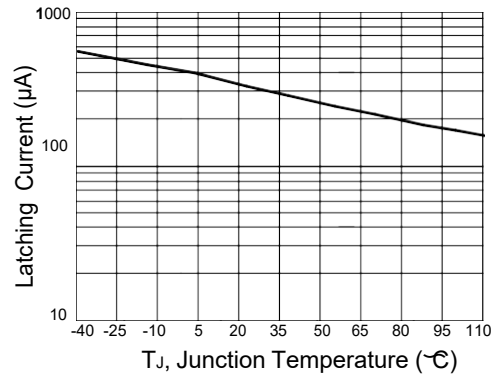
**Figure 1. Typical Gate Trigger Current Versus Junction Temperature**



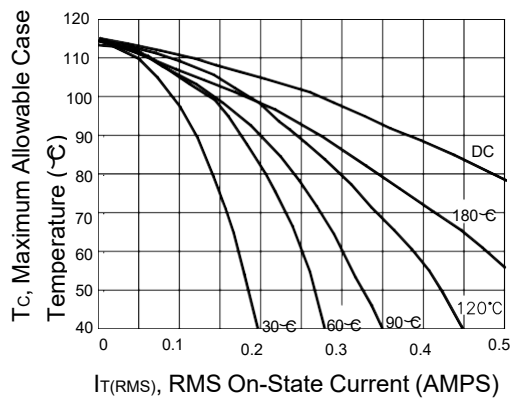
**Figure 2. Typical Gate Trigger Voltage Versus Junction Temperature**



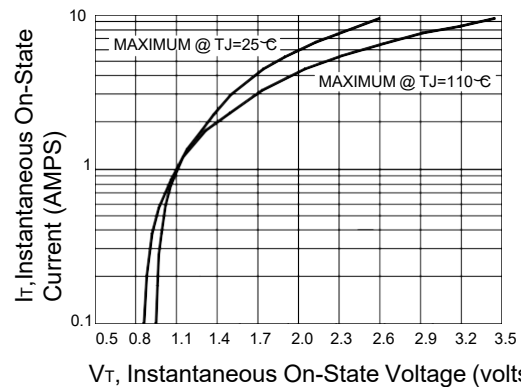
**Figure 3. Typical Holding Current Versus Junction Temperature**



**Figure 4. Typical Latching Current Versus Junction Temperature**



**Figure 5. Typical RMS Current Derating**

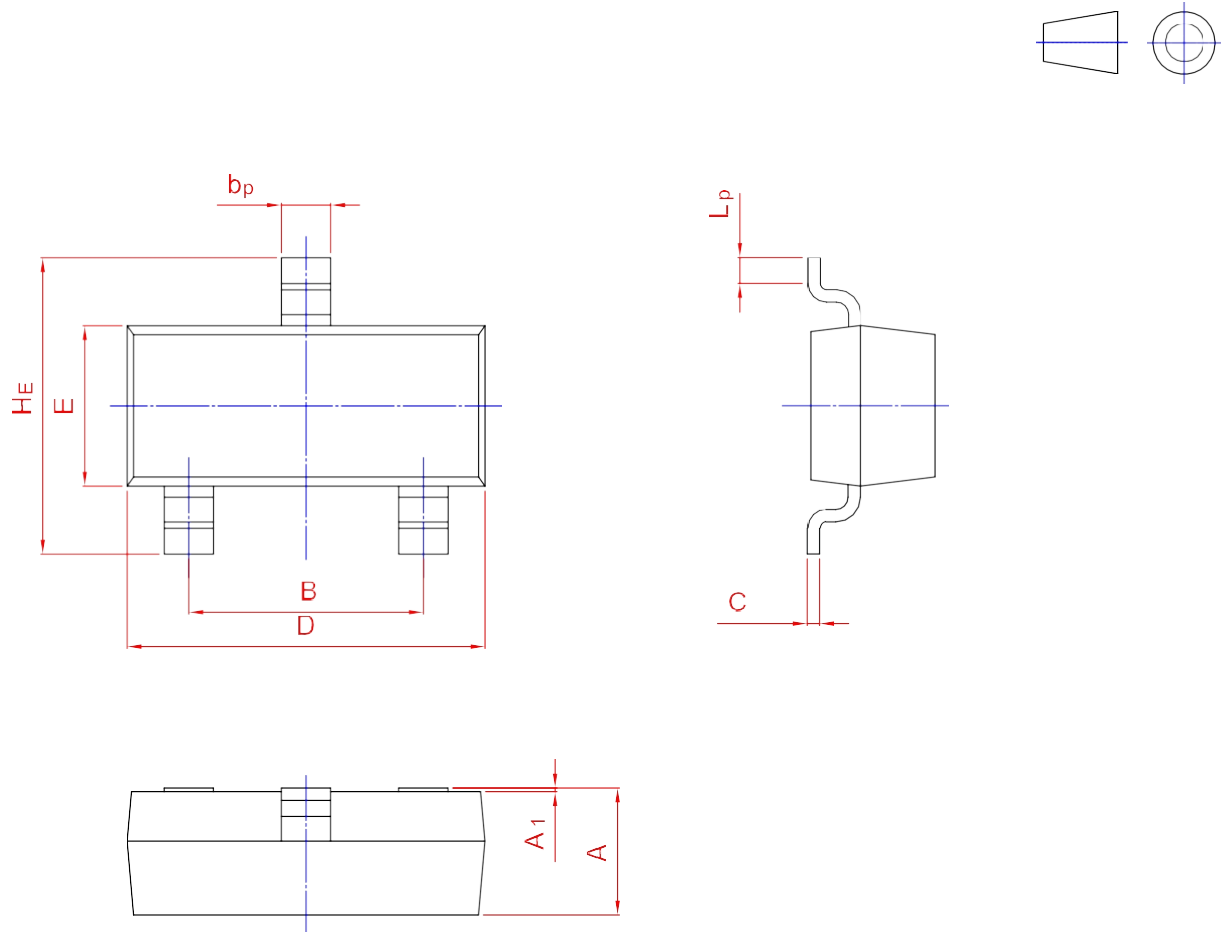


**Figure 6. Typical On-State Characteristics**

## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



| UNIT | A            | B            | b <sub>p</sub> | C            | D            | E            | H <sub>E</sub> | A <sub>1</sub> | L <sub>p</sub> |
|------|--------------|--------------|----------------|--------------|--------------|--------------|----------------|----------------|----------------|
| mm   | 1.40<br>0.95 | 2.04<br>1.78 | 0.50<br>0.35   | 0.19<br>0.08 | 3.10<br>2.70 | 1.65<br>1.20 | 3.00<br>2.20   | 0.100<br>0.013 | 0.50<br>0.20   |